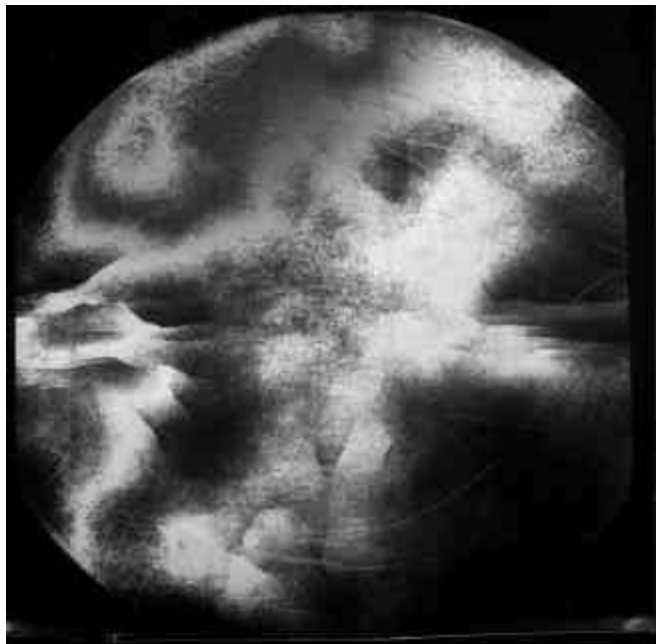




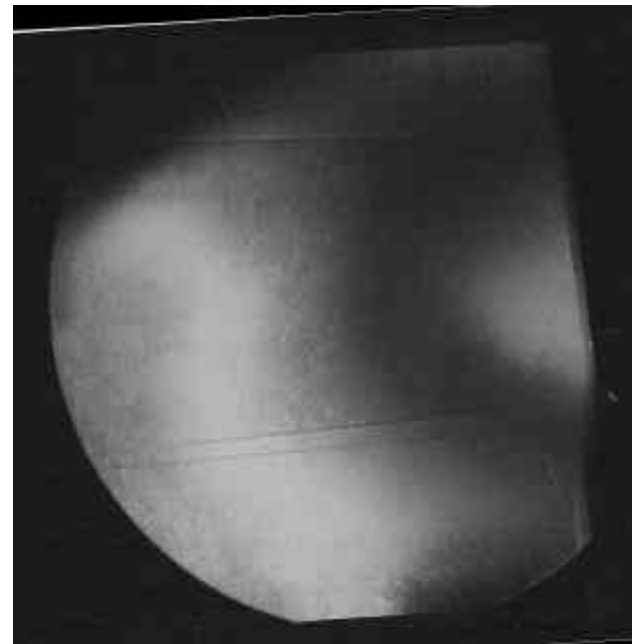
XRT: LEC vs. VB

LEC



(a)

VB

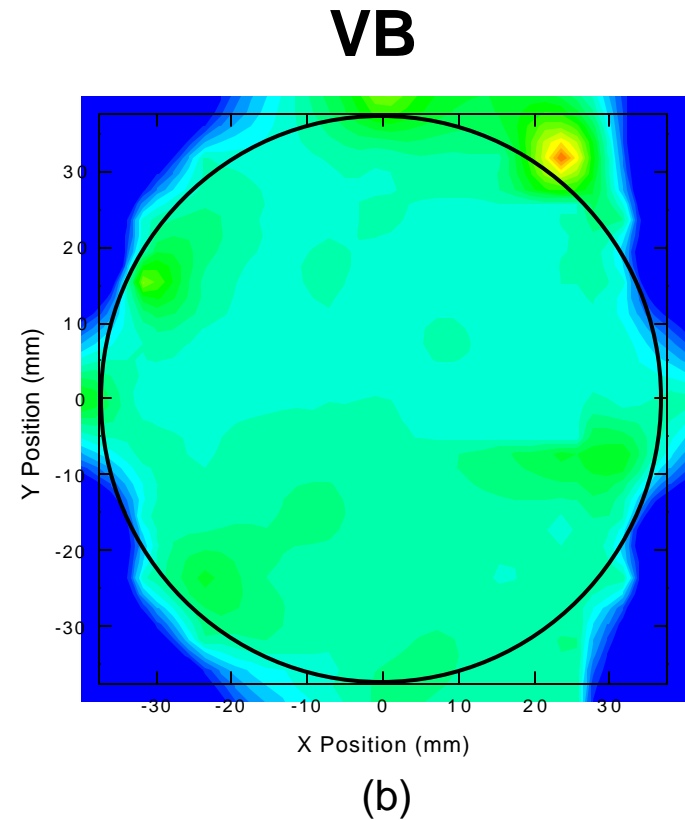
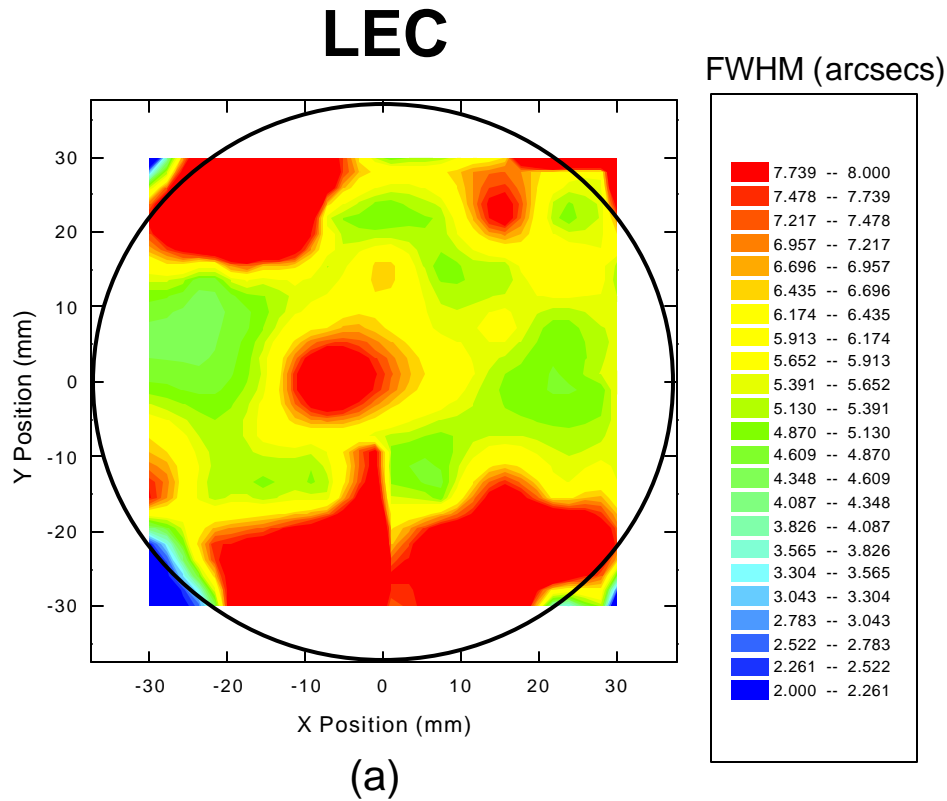


(b)

(a) shows the x-ray topograph of a 3 inch SI LEC grown GaAs wafer, whereas (b) shows the x-ray topograph of a 3 inch SI VB grown GaAs wafer. The x-ray topograph for the LEC grown wafer shows sharp tilt lines and abrupt changes in intensity across the wafer surface. On the other hand the x-ray topograph for the VB shows uniform contrast across most of the wafer surface and the absence of any gross features as observed in the



w-mapping: LEC vs. VB



Wafer
LEC
VB

Average full width at half maximum (arcseconds)
7.5

Standard Deviation (arcseconds)
0.6